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電源管理



顯示驅動



二三極管



LDO穩壓器



觸摸芯片



MOS管



運算放大器



存儲芯片



MCU



串口通信

1N4004WS T7-TD

產品規格說明書

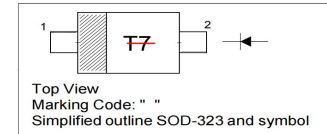
1N4007WS Silicon Epitaxial Planar Switching Diode

Features

- SOD-323 package

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

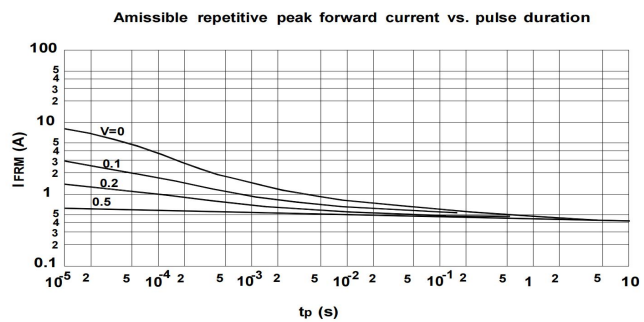
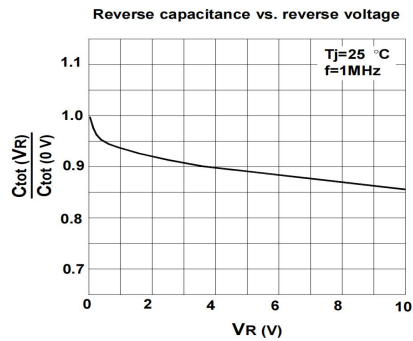
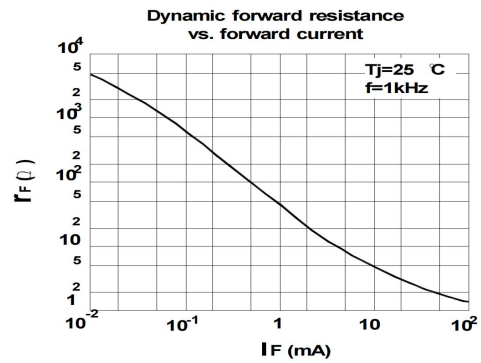
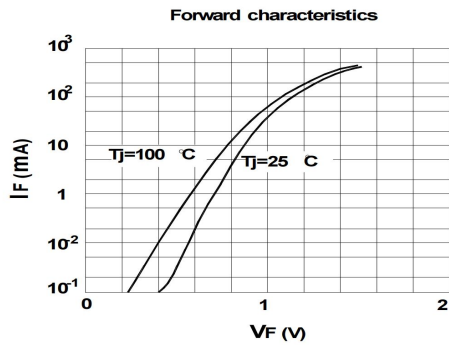


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	200	V
Reverse Voltage	V_R	100	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Surge Forward Current ($t < 1\text{ s}$, $T_j = 25^\circ\text{C}$)	I_{FSM}	350	mA
Power Dissipation	P_{tot}	200	mW
Thermal Resistance from Junction to Ambient Air	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 1\text{ }\mu\text{A}$	$V_{(BR)R}$	100	-	V
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 50\text{ mA}$ at $I_F = 150\text{ mA}$	V_F	- - - -	0.715 0.855 1 1.25	V
Peak Reverse Current at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$, $T_j = 150^\circ\text{C}$ at $V_R = 25\text{ V}$, $T_j = 150^\circ\text{C}$	I_R	- - - -	1 25 50 30	μA nA μA μA
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	-	2	pF
Reverse Recovery Time at $I_{rr} = 0.1 \times I_R$, $I_F = I_R = 10\text{ mA}$, $R_L = 100\text{ }\Omega$	t_{rr}	-	4	ns



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

